

Publikačný seminár

P. Chauhan:

Evidence of relationship between strain and In-incorporation: Growth of N-polar In-rich InAlN buffer layer by OMCVD
Journal of Applied Physics

J. Kuzmík:

Generation of hole gas in non-inverted InAl(Ga)N/GaN heterostructures
Applied Physics Express

Z. Zápražný:

Characterization of the chips generated by the nanomachining of germanium for X-ray crystal optics
International Journal of Advanced Manufacturing Technology

Š. Chromik:

Some peculiarities at preparation of Bi₄Ti₃O₁₂ films for bolometric applications
Applied Surface Science

Čas: 29. marec 2019 o 10:00 hod. Miesto: veľká zasadačka EIÚ SAV, miestnosť 101